

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7WH00FU, TC7WH00FK

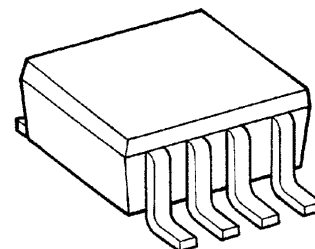
DUAL 2-INPUT NAND GATE

The TC7WH00 is an advanced high speed CMOS 2-INPUT NAND GATE fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

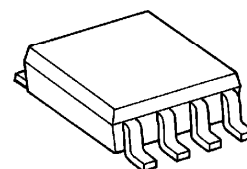
- High Speed $t_{pd} = 3.7\text{ns}$ (Typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation $I_{CC} = 2\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC}(\text{opr}) = 2 \sim 5.5\text{V}$

TC7WH00FU



SSOP8-P-0.65

TC7WH00FK

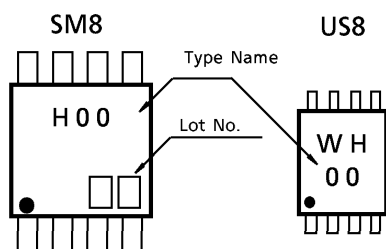


SSOP8-P-0.50A

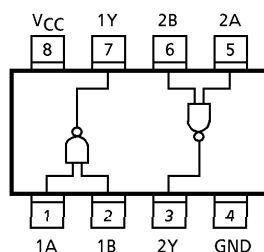
Weight

SSOP8-P-0.65 : 0.02g (Typ.)
 SSOP8-P-0.50A : 0.01g (Typ.)

MARKING



PIN ASSIGNMENT (TOP VIEW)



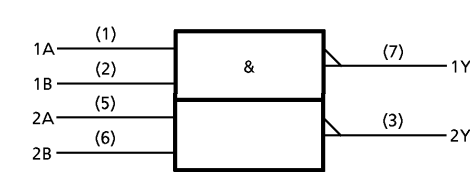
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	− 0.5~7.0	V
DC Input Voltage	V _{IN}	− 0.5~7.0	V
DC Output Voltage	V _{OUT}	− 0.5~V _{CC} + 0.5	V
Input Diode Current	I _{IK}	− 20	mA
Output Diode Current	I _{OK}	± 20	mA
DC Output Current	I _{OUT}	± 25	mA
DC V _{CC} / Ground Current	I _{CC}	± 50	mA
Power Dissipation	P _D	300 (SM8)	mW
		200 (US8)	
Storage Temperature	T _{stg}	− 65~150	°C
Lead Temperature (10 s)	T _L	260	°C

LOGIC DIAGRAM



TRUTH TABLE

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	2.0~5.5	V
Input Voltage	V _{IN}	0~5.5	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	− 40~85	°C
Input Rise and Fall Time	dt / dv	0~100 (V _{CC} = 3.3 ± 0.3V)	ns / V
		0~20 (V _{CC} = 5 ± 0.5V)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	V _{IH}	—		2.0	1.50	—	—	1.50	—	V
				3.0~5.5	V _{CC} × 0.7	—	—	V _{CC} × 0.7	—	
Low-Level Input Voltage	V _{IL}	—		2.0	—	—	0.50	—	0.50	V
				3.0~5.5	—	—	V _{CC} × 0.3	—	V _{CC} × 0.3	
High-Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
			I _{OH} = -4mA	3.0	2.58	—	—	2.48	—	
			I _{OH} = -8mA	4.5	3.94	—	—	3.80	—	
Low-Level Output Voltage	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 50 μA	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
			I _{OL} = 4mA	3.0	—	—	0.36	—	0.44	
			I _{OL} = 8mA	4.5	—	—	0.36	—	0.44	
Input Leakage Current	I _{IN}	V _{IN} = 5.5V or GND		0~5.5	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	2.0	—	20.0	μA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = - 40~85°C		UNIT
			V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t _{pLH} t _{pHL}	—	3.3 ± 0.3	15	—	5.5	7.9	1.0	9.5	ns
				50	—	8.0	11.4	1.0	13.0	
			5.0 ± 0.5	15	—	3.7	5.5	1.0	6.5	
				50	—	5.2	7.5	1.0	8.5	
Input Capacitance	C _{IN}	—			—	4	10	—	10	pF
Power Dissipation Capacitance	C _{PD}	(Note 1)			—	19	—	—	—	pF

(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

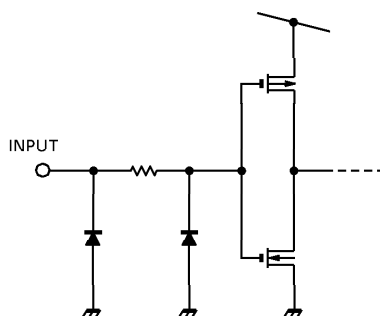
Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

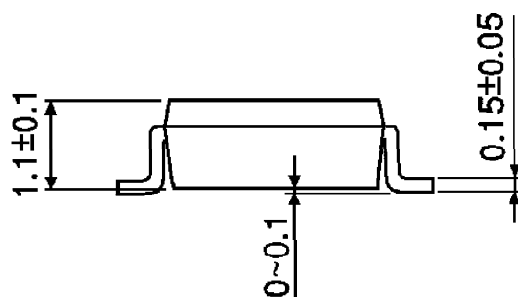
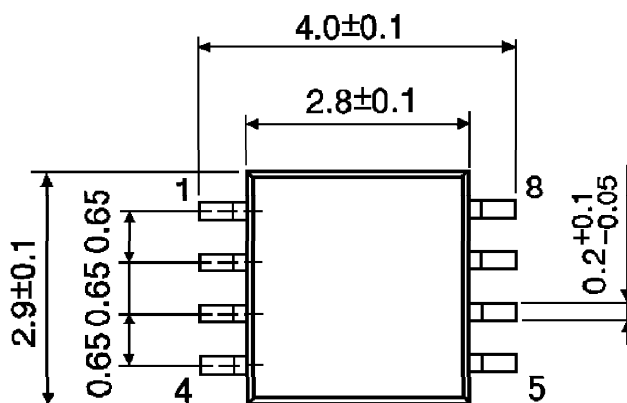
NOISE CHARACTERISTICS (Ta = 25°C, Input $t_r = t_f = 3\text{ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	C _L = 50pF	5.0	0.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	C _L = 50pF	5.0	− 0.3	− 0.8	V
Minimum High Level Dynamic Input Voltage	V _{IHD}	C _L = 50pF	5.0	—	3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}	C _L = 50pF	5.0	—	1.5	V

INPUT EQUIVALENT CIRCUIT



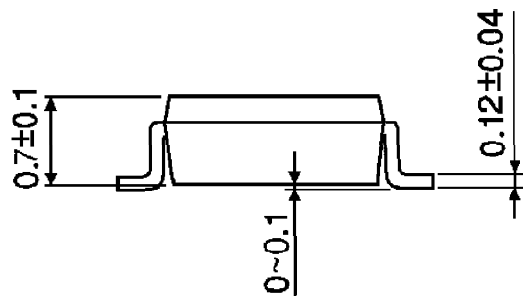
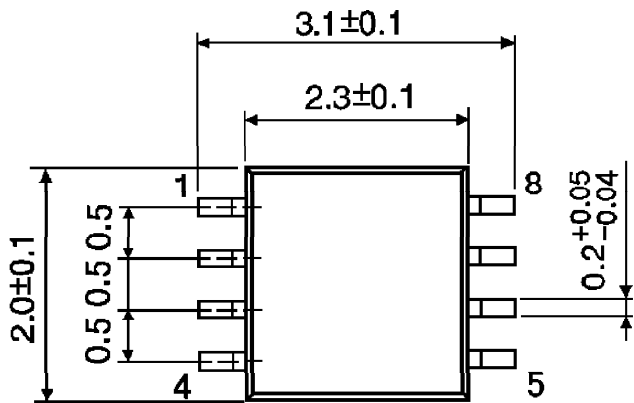
Unit : mm



Weight : 0.02g (Typ.)

PACKAGE DIMENSIONS
SSOP8-P-0.50A

Unit : mm



Weight : 0.01g (Typ.)